

3mm Silicon Phototransistor

PT8294-6B

Features

- Fast response time
- High photo sensitivity
- Pb free
- This product itself will remain within RoHS compliant version.

Descriptions

- PT8294-6B is a high speed and high sensitive NPN silicon phototransistor molded in a standard $\phi 3$ mm package. Due to its black epoxy the device is sensitive to visible and near infrared radiation..

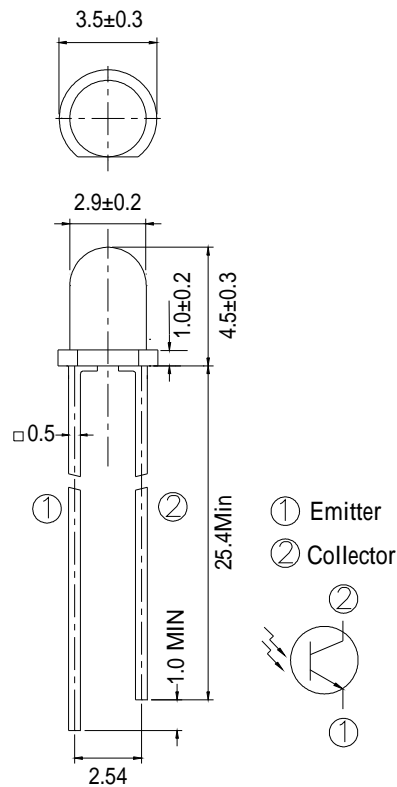
Applications

- Camera
- Infrared applied system

Device Selection Guide

LED Part No.	Chip	Lens Color
	Material	
PT	Silicon	Black

Package Dimensions



- Notes:** 1.All dimensions are in millimeters
2.Tolerances unless dimensions $\pm 0.25\text{mm}$

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector-Voltage	V_{ECO}	5	V
Collector Current	I_C	20	mA
Operating Temperature	T_{opr}	-25 ~ +85	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 ~ +100	$^\circ\text{C}$
Lead Soldering Temperature*1	T_{sol}	260	$^\circ\text{C}$
Power Dissipation at (or below) 25 Free Air Temperature	P_c	75	mW

Notes: *1:Soldering time 5 seconds.

Electro-Optical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Collector – Emitter Breakdown Voltage	BV_{CEO}	$I_C=100 \mu A$ $E_e=0mW/cm^2$	30	---	---	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	$I_E=100 \mu A$ $E_e=0mW/cm^2$	5	---	---	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2mA$ $E_e=1mW/cm^2$	---	---	0.4	V
Rise Time	t_r	$V_{CE}=5V$ $I_C=mA$ $RL=1000$	---	15	---	μS
Fall Time	t_f		---	15	---	
Collector Dark Current	I_{CEO}	$E_e=0mW/cm^2$ $V_{CE}=20V$	---	---	100	nA
On State Collector Current	$I_{C(on)}$	$E_e=1mW/cm^2$ $V_{CE}=5V$	0.7	1.8	---	mA
Wavelength of Peak Sensitivity	p	---	---	940	---	nm
Rang of Spectral Bandwidth	0.5	---	---	760-1100	---	nm

Rankings

Parameter	Symbol	Min	Max	Unit	Test Condition
G	$I_{C(ON)}$	0.70	1.90	mA	$V_{CE}=5V$ $E_e=1mW/cm^2$
H		1.14	2.60		
J		1.77	3.61		
K		2.67	5.07		

Typical Electro-Optical Characteristics Curves

Fig.1 Collector Power Dissipation vs. Ambient Temperature

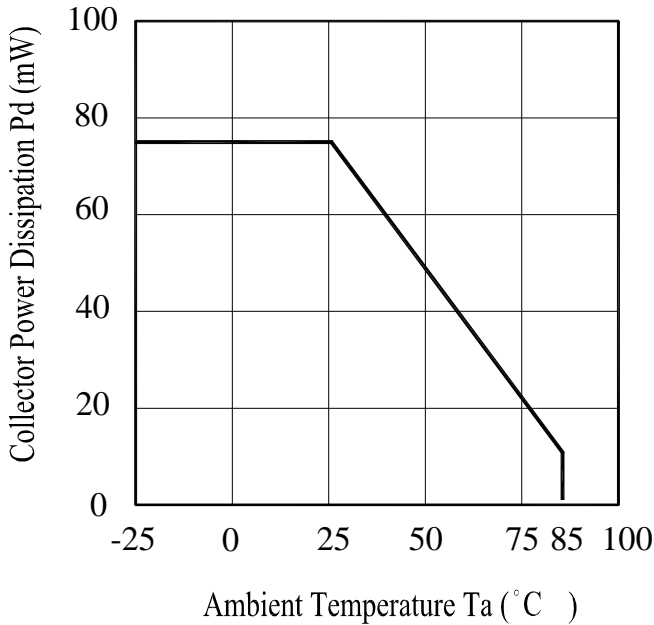


Fig.2 Spectral Sensitivity

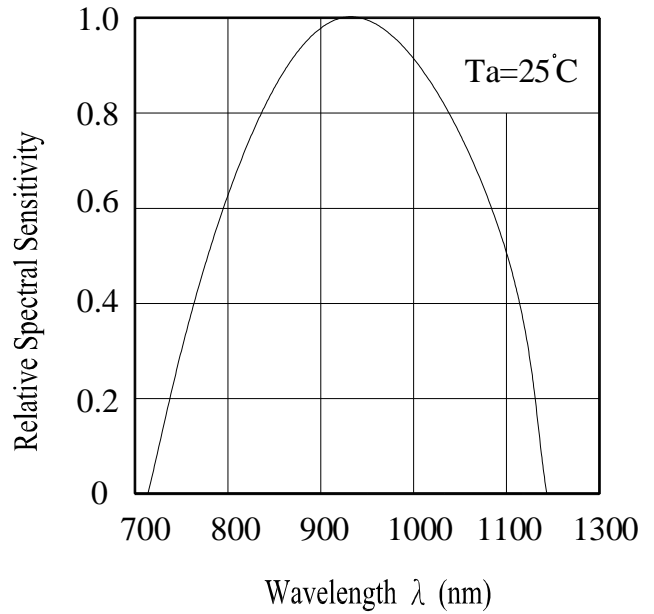


Fig.3 Relative Collector Current vs. Ambient Temperature

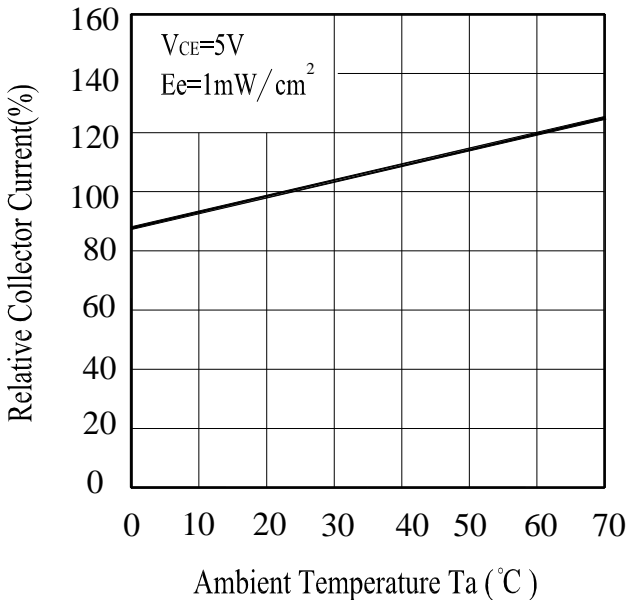
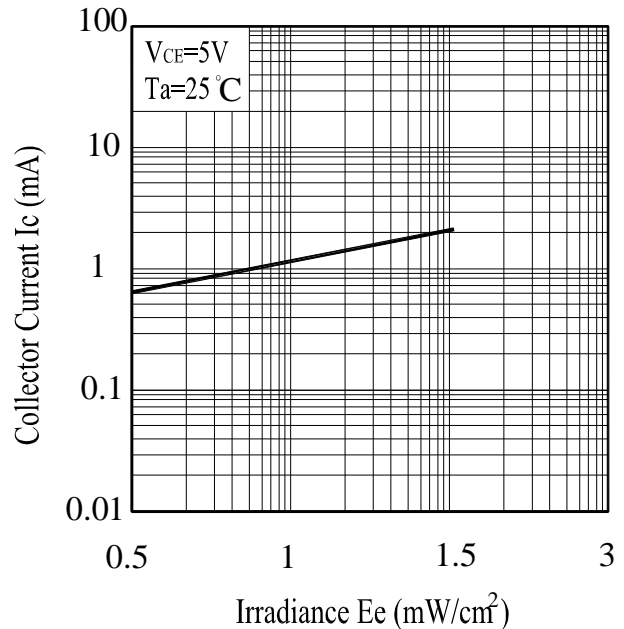


Fig.4 Collector Current vs. Irradiance



Typical Electro-Optical Characteristics Curves

Fig.5 Collector Dark Current vs. Ambient Temperature

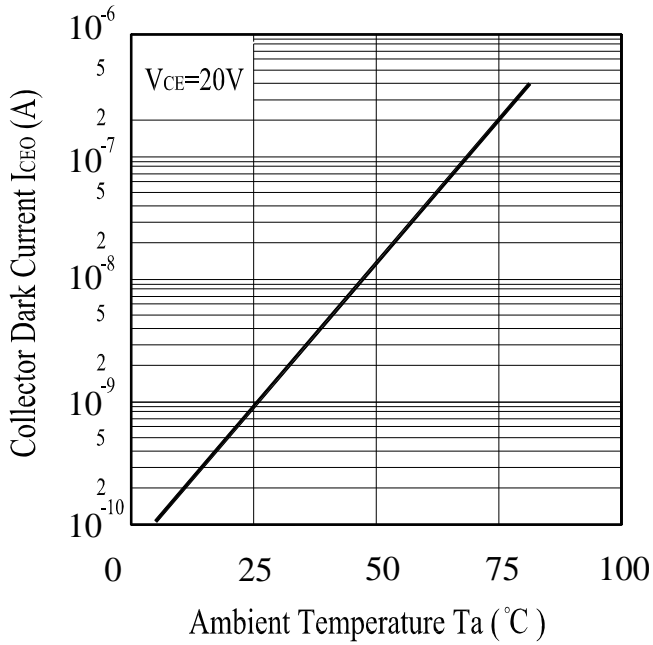
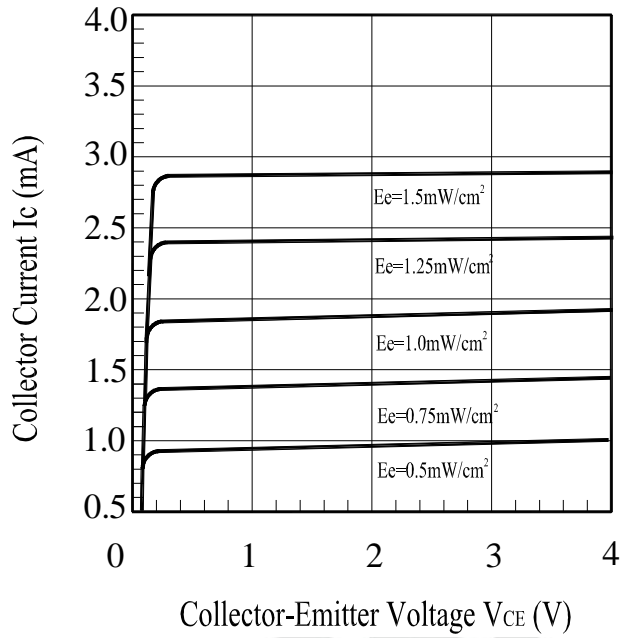


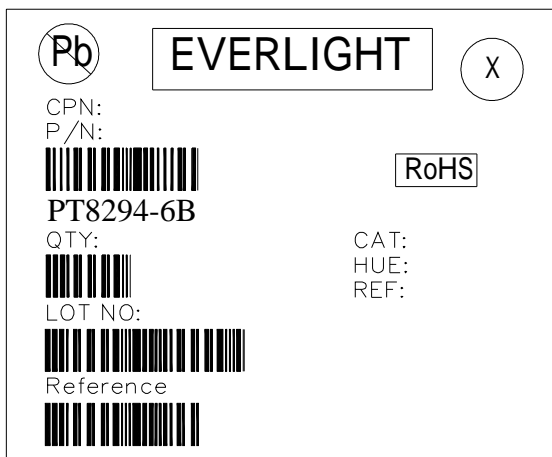
Fig.6 Collector Current vs. Collector-Emitter Voltage



Packing Quantity Specification

1. 1000Pcs/Bags , 4Bags/1Boxes
2. 10Boxes/1Carton

Label Form Specification



CPN: Customer's Production Number

P/N : Production Number

QTY: Packing Quantity

CAT: Ranks

HUE: Peak Wavelength

REF: Reference

LOT No: Lot Number

X: Month

Reference: Identify Label Number

Notes

1. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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